

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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 APPLICANT  
**Makoto KITABATAKE, et al.**

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 GROUP  
**2814**

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number 4-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
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## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		LUTZ et al., Technische Universitat Chemnitz, "Stand und Entwicklungstendenzen bei schnellen Dioden," 20020301, 1 March 2002 (2002-03-01), XP002491991; and partial English translation thereof
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		Supplementary European Search Report issued in Patent Application No. 04772945.4-1235/1596434 PCT/JP2004013263 dated on August 27, 2008

EXAMINER

DATE CONSIDERED

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